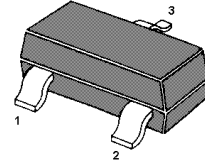


MMBTSA1365

PNP Silicon Epitaxial Planar Transistor

for high current drive application

The transistor is subdivided into three groups E, F and G according to its DC current gain.



1.BASE 2.EMITTER 3.COLLECTOR
SOT-23 Plastic Package

Absolute Maximum Ratings ($T_a = 25\text{ }^\circ\text{C}$)

Parameter	Symbol	Value	Unit
Collector Base Voltage	$-V_{CBO}$	25	V
Collector Emitter Voltage	$-V_{CEO}$	20	V
Emitter Base Voltage	$-V_{EBO}$	4	V
Collector Current	$-I_C$	700	mA
Peak Collector Current	$-I_{CM}$	1	A
Power Dissipation	P_{tot}	200	mW
Junction Temperature	T_j	150	$^\circ\text{C}$
Storage Temperature Range	T_{Stg}	- 55 to + 150	$^\circ\text{C}$

Characteristics at $T_a = 25\text{ }^\circ\text{C}$

Parameter	Symbol	Min.	Typ.	Max.	Unit	
DC Current Gain at $-V_{CE} = 4\text{ V}$, $-I_C = 100\text{ mA}$	E	h_{FE}	150	-	300	-
	F	h_{FE}	250	-	500	-
	G	h_{FE}	400	-	800	-
Collector Cutoff Current at $-V_{CB} = 25\text{ V}$	$-I_{CBO}$	-	-	1	μA	
Emitter Cutoff Current at $-V_{EB} = 2\text{ V}$	$-I_{EBO}$	-	-	1	μA	
Collector Base Breakdown Voltage at $-I_C = 10\text{ }\mu\text{A}$	$-V_{(BR)CBO}$	25	-	-	V	
Collector Emitter Breakdown Voltage at $-I_C = 100\text{ }\mu\text{A}$	$-V_{(BR)CEO}$	20	-	-	V	
Emitter Base Breakdown Voltage at $-I_E = 10\text{ }\mu\text{A}$	$-V_{(BR)EBO}$	4	-	-	V	
Collector Saturation Voltage at $-I_C = 500\text{ mA}$, $-I_B = 25\text{ mA}$	$-V_{CE(sat)}$	-	-	0.5	V	
Transition Frequency at $-V_{CE} = 6\text{ V}$, $I_E = 10\text{ mA}$	f_T	-	180	-	MHz	

TOP DYNAMIC



ISO14001 : 2004 Certificate No. 121505007
ISO 9001 : 2008 Certificate No. 50114912
OHSAS 18001 : 2007 Certificate No. 05131508008
IECQ QC 080000 Certificate No. 0204100014402

Dated : 06/12/2012

